

Product Features

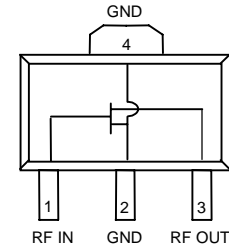
- 50 – 3000 MHz
- 13.5 dB Gain
- +26 dBm P1dB
- +37 dBm OIP3
- 2.0 dB Noise Figure
- MTTF > 100 years
- SOT-89 SMT Package

Product Description

The FP101 is a high dynamic range GaAs FET packaged in a low-cost surface-mount package. The combination of low noise figure and high output IP3 at the same bias point makes it ideal for receiver and transmitter applications. The FP101 achieves +37 dBm OIP3 with consistent quality to maintain MTTF values exceeding 100 years at mounting temperatures of +85°C and is housed in a SOT-89 industry-standard SMT package.

All devices are 100% RF and DC tested. The product is targeted for applications where high linearity is required.

Functional Diagram



Function	Pin No.
Input / Gate	1
Output / Drain	3
Ground	2, 4

Specification

DC Parameter	Units	Min	Typ	Max	Comments
Saturated Drain Current, I_{dss}	mA		270		$V_{gs} = 0\text{ V}$, $V_{ds} = 3\text{ V}$
Transconductance, G_m	mS		120		
Pinch Off Voltage, V_p	V		-2.3		$I_{ds} = 1.2\text{ mA}$

RF Parameter	Units	Min	Typ	Max	Comments
Frequency Range	MHz	50	800	3000	
Small Signal Gain, G_{ss}	dB		13.5		
Maximum Stable Gain, G_{msg}	dB		20.5		
Output P1dB	dBm	+23	+26		
Output IP3	dBm	+34	+37		+8 dBm / tone, 10 MHz spacing, 1850 MHz
Noise Figure	dB		1.9		$V_{ds} = +5\text{ V}$

Test conditions unless otherwise noted: $T = 25^\circ\text{C}$, $V_{gs} = +8\text{ V}$, $I_{dq} = 100\text{ mA}$, frequency = 800 MHz in a 50 ohm system.

Thermal Information

Parameters	Rating
Operating Case Temperature	-40 to +85° C
Storage Temperature	-55 to +125° C
Thermal Resistance (junction to ground tab)	68° C / W
Junction Temperature* (8V / 100 mA)	139° C
Junction Temperature* (5V / 100 mA)	119° C

* A minimum MTTF of 1 million hours is achieved for junction temperatures below 160° C.

Absolute Maximum Rating

Parameters	Rating
Gate to Source Voltage	-6 V
RF Input Power (continuous)	+17 dBm
DC Power	2.0 W
Junction Temperature	+220° C

Operation of this device above any of these parameters may cause permanent damage.

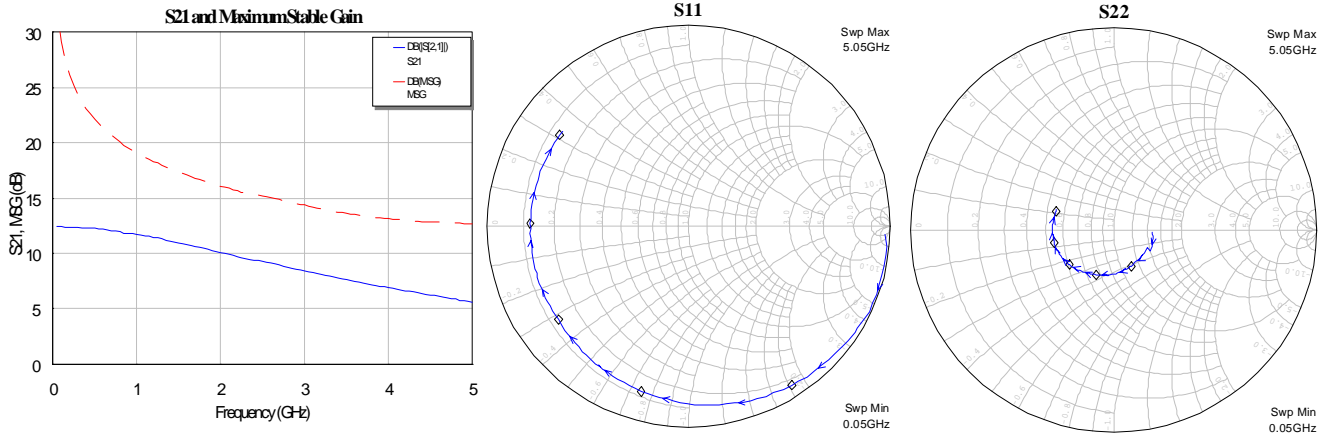
Ordering Information

Part No.	Description
FP101	High Dynamic Range FET

Specifications and information are subject to change without notice.

Typical Device Data

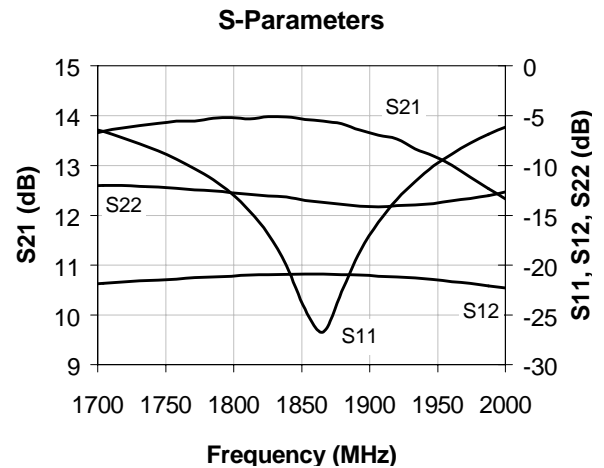
S-Parameters ($V_{ds} = 8\text{ V}$, $I_{ds} = 100\text{ mA}$, 25°C , Unmatched 50 ohm system)



Reference Design (1800 – 1900 MHz)

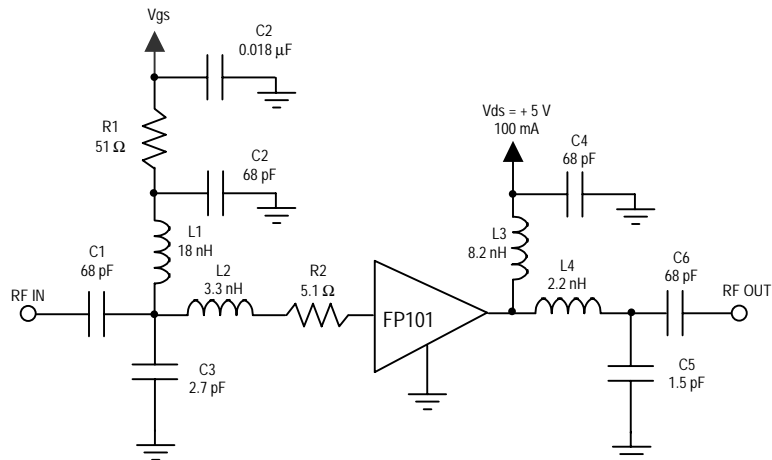
Typical Performance

Parameter	Value	Comments
Frequency	1850 MHz	
S21 - Gain	13.9 dB	
S11 - Input Return Loss	-23.6 dB	
S22 - Output Return Loss	-13.5 dB	
S12 - Isolation	-20.9 dB	
Output IP3	36.2 dBm	See Note 1, 3
Output P1dB	23.3 dBm	See Note 3
Noise Figure	3.6 dB	
Drain Bias	5 V @ 100 mA	



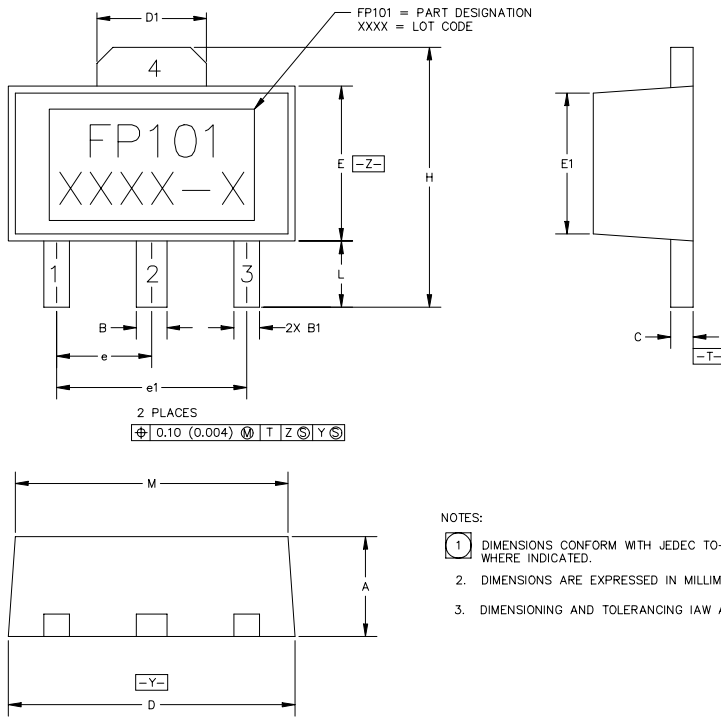
Notes

- OIP3 is measured with 2 tones at an output power of +10 dBm/tone with 10 MHz spacing at 1850 MHz. The suppression on the largest IM3 product is used to calculate OIP3 using a 2:1 slope rule. Test parameters were taken at 25°C .
- All components are 0603 size. Toko LL1608-FH chip inductors and AVX $\pm 0.1\text{ pF}$ tolerance capacitors (C3 and C5) were used in the design. Other capacitor components are standard types. The overall circuit size should be minimized as much as possible.
- The drain voltage can be increased to +8 V for increased output power performance (higher P1dB, higher OIP3). The gate voltage can be adjusted so that the drain bias can be anywhere between 50 - 150 mA.



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Outline Drawing

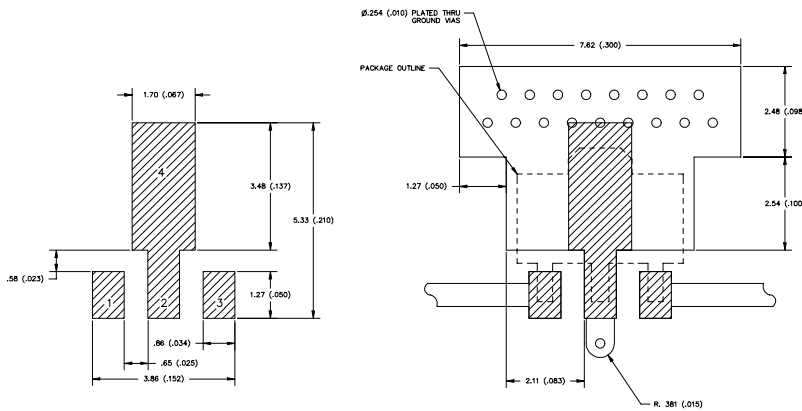


Product Marking

The component will be marked with an “FP101” designator with a four- or five-digit alphanumeric lot code on the top surface of the package. Tape and reel specifications for this part is located on the website in the “Application Notes” section.

SYMBOL	MIN	MAX
A	1.40 (.055)	1.60 (.063)
B	.44 (.017)	.56 (.022)
B1	.36 (.014)	.48 (.019)
C	.35 (.014)	.44 (.017)
D	4.40 (.173)	4.60 (.181)
D1	1.62 (.064)	1.83 (.072)
E	2.29 (.090)	2.60 (.102)
E1	2.01 (.079)	2.29 (.090)
e	1.50 BSC (.059)	
e1	3.00 BSC (.118)	
H	3.94 (.155)	4.25 (.167)
L	.89 (.035)	1.20 (.047)
M	4.04 (.159)	4.19 (.165)

Land Pattern



ESD / MSL Information

ESD Classification: Class 1C
 Value: Passes ≥ 1000 V to <2000 V
 Test: Human Body Model (HBM)
 Standard: JEDEC Standard JESD22-A114

ESD Classification: Class IV
 Value: Passes ≥ 1000 V
 Test: Charged Device Model (CDM)
 Standard: JEDEC Standard JESD22-C101

MSL Rating: Level 3 at +235 °C convection reflow
 Standard: JEDEC Standard J-STD-020A

Mounting Config. Notes

1. Ground / thermal vias are critical for the proper performance of this device. Vias should use a .35mm (#80 / .0135”) diameter drill and have a final plated thru diameter of .25 mm (.010”).
2. Add as much copper as possible to inner and outer layers near the part to ensure optimal thermal performance.
3. Mounting screws can be added near the part to fasten the board to a heatsink. Ensure that the ground / thermal via region contacts the heatsink.
4. Do not put solder mask on the backside of the PC board in the region where the board contacts the heatsink.
5. RF trace width depends upon the PC board material and construction.
6. Use 1 oz. Copper minimum.
7. All dimensions are in millimeters (inches). Angles are in degrees.

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Typical Device Data

S-Parameters ($V_D = +5\text{ V}$, $I_D = 100\text{ mA}$, $T = 25^\circ\text{C}$, calibrated to device leads)

Freq (MHz)	S11 (dB)	S11 (ang)	S21 (dB)	S21 (ang)	S12 (dB)	S12 (ang)	S22 (dB)	S22 (ang)
200	-0.05	-11.65	13.09	170.35	-40.11	83.52	-20.18	-20.22
400	-0.03	-23.12	13.00	161.72	-33.94	77.88	-18.83	-41.57
600	-0.18	-36.31	12.87	151.32	-30.39	68.68	-19.57	-59.31
800	-0.32	-47.17	12.65	142.63	-28.11	61.81	-18.20	-76.47
1000	-0.50	-58.15	12.38	133.74	-26.38	55.76	-17.00	-91.39
1200	-0.67	-69.49	12.09	125.22	-25.12	48.54	-16.25	-103.87
1400	-0.88	-79.35	11.76	117.41	-24.03	42.65	-15.13	-112.58
1600	-0.99	-89.35	11.43	109.46	-23.28	36.62	-14.26	-121.97
1800	-1.21	-98.68	11.04	101.95	-22.60	30.96	-13.77	-129.80
2000	-1.33	-107.48	10.68	94.92	-21.97	25.56	-13.13	-136.00
2200	-1.53	-116.22	10.30	87.87	-21.48	20.05	-12.63	-142.70
2400	-1.67	-124.67	9.94	81.13	-21.06	14.86	-12.13	-148.50
2600	-1.74	-129.96	9.70	76.55	-20.80	11.41	-11.84	-152.37
2800	-1.87	-137.82	9.34	70.28	-20.44	6.62	-11.55	-157.82
3000	-1.97	-146.08	9.01	64.05	-20.22	0.76	-11.24	-162.58

S-Parameters ($V_D = +8\text{ V}$, $I_D = 100\text{ mA}$, $T = 25^\circ\text{C}$, calibrated to device leads)

Freq (MHz)	S11 (dB)	S11 (ang)	S21 (dB)	S21 (ang)	S12 (dB)	S12 (ang)	S22 (dB)	S22 (ang)
200	-0.11	-11.45	12.37	170.42	-39.98	79.95	-14.10	-12.80
400	-0.09	-22.71	12.28	161.78	-33.90	76.01	-13.71	-26.74
600	-0.24	-35.70	12.17	151.43	-30.61	67.68	-14.51	-36.99
800	-0.38	-46.35	11.97	142.64	-28.17	61.30	-14.24	-50.43
1000	-0.53	-57.07	11.72	133.73	-26.47	54.53	-14.01	-63.83
1200	-0.70	-68.34	11.44	125.17	-25.18	47.72	-13.94	-74.67
1400	-0.90	-77.99	11.13	117.20	-24.20	41.43	-13.43	-85.29
1600	-1.02	-88.00	10.81	109.14	-23.36	35.88	-13.06	-95.56
1800	-1.24	-97.21	10.43	101.55	-22.67	30.53	-12.84	-104.03
2000	-1.35	-105.96	10.08	94.34	-22.13	25.25	-12.44	-111.54
2200	-1.54	-114.67	9.70	87.18	-21.60	20.06	-12.16	-119.40
2400	-1.69	-123.07	9.35	80.34	-21.19	14.79	-11.82	-126.07
2600	-1.76	-128.30	9.11	75.57	-20.96	11.26	-11.63	-130.63
2800	-1.89	-136.04	8.76	69.16	-20.59	6.53	-11.40	-136.59
3000	-2.00	-144.31	8.43	62.87	-20.35	1.69	-11.16	-141.99